

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Jong-Lam LEE

Serial No.: Not yet assigned Group Art Unit: Not yet assigned

Filed: July 14, 2006 Examiner: Not yet assigned

For: GALLIUM NITRIDE-BASED III-V GROUP COMPOUND
SEMICONDUCTOR DEVICE AND METHOD FO MANUFACTURING THE
SAME

INFORMATION DISCLOSURE CITATION
FORM PTO-1449 (Modified)U.S. PATENT DOCUMENTS

<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>Document</u> <u>Number</u>	<u>Issue</u> <u>Date</u>	<u>Name</u>	<u>Class</u>	<u>Sub</u> <u>Class</u>
----------------------------	------------	----------------------------------	-----------------------------	-------------	--------------	----------------------------

FOREIGN PATENT DOCUMENTS

<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>Document</u> <u>Number</u>	<u>Publication</u> <u>Date</u>	<u>Country</u>	<u>Name</u>
_____	_____	11-40846	Feb. 12, 99	Japan	Hisanaga Yukihiro, et al.
_____	_____	2000-36619	Feb. 2, 00	Japan	Kamimura Toshiya
_____	_____	2000-294837	Oct. 20, 00	Japan	Sato Hiroyuki, et al.
_____	_____	WO 02/099901 A1	Dec. 12, 02	PCT	Uemura Toshiya

OTHER DOCUMENTS

<u>Exam</u> <u>Init</u>	<u>Ref</u>	<u>Author, Title, Date, Pertinent Pages, Etc.)</u>
_____	_____	English language abstract of Japanese Publication No. 11-40846
_____	_____	English language abstract of Japanese Publication No. 2000-36619
_____	_____	English language abstract of Japanese Publication No. 2000-294837

Examiner: _____/Thinh Nguyen/

Date Considered: 03/27/2009

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /T.N./